

LM330 3-Terminal Positive Regulator

General Description

The LM330 5V 3-terminal positive voltage regulator features an ability to source 150 mA of output current with an input-output differential of 0.6V or less. Familiar regulator features such as current limit and thermal overload protection are also provided.

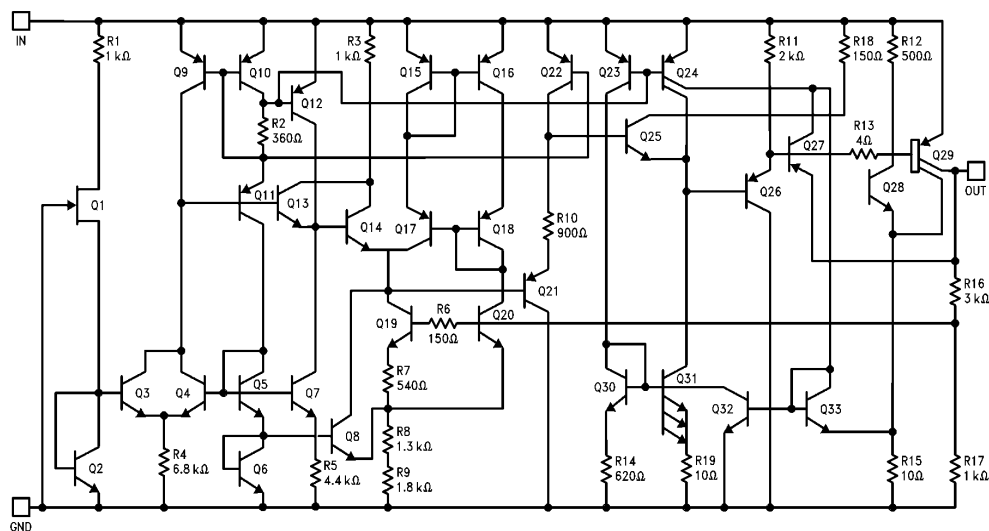
The low dropout voltage makes the LM330 useful for certain battery applications since this feature allows a longer battery discharge before the output falls out of regulation. For example, a battery supplying the regulator input voltage may discharge to 5.6V and still properly regulate the system and load voltage. Supporting this feature, the LM330 protects both itself and regulated systems from negative voltage inputs resulting from reverse installations of batteries.

Other protection features include line transient protection up to 26V, when the output actually shuts down to avoid damaging internal and external circuits. Also, the LM330 regulator cannot be harmed by a temporary mirror-image insertion.

Features

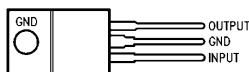
- Input-output differential less than 0.6V
- Output current of 150 mA
- Reverse battery protection
- Line transient protection
- Internal short circuit current limit
- Internal thermal overload protection
- Mirror-image insertion protection
- P+ Product Enhancement tested

Schematic and Connection Diagrams



TL/H/9306-1

(TO-220)
Plastic Package



TL/H/9306-2

Front View

Order Number LM330T-5.0
See NS Package Number T03B

Absolute Maximum Ratings

If Military/Aerospace specified devices are required, please contact the National Semiconductor Sales Office/Distributors for availability and specifications.

Input Voltage	
Operating Range	26V
Line Transient Protection (1000 ms)	40V

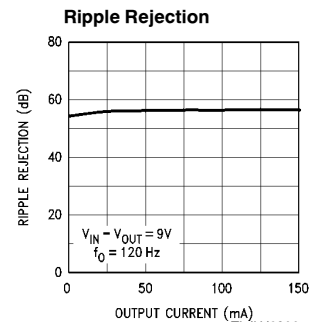
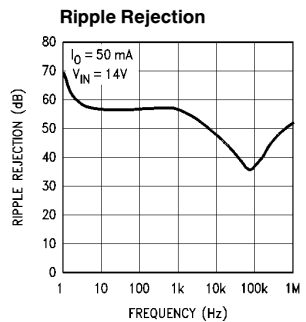
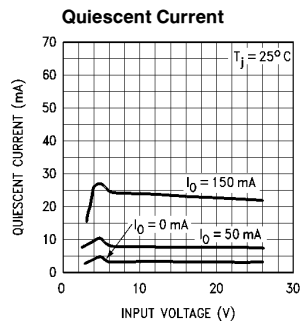
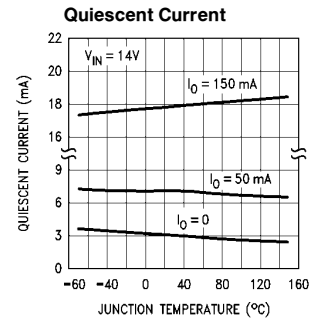
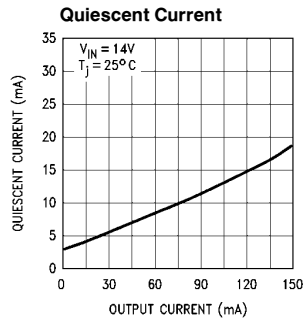
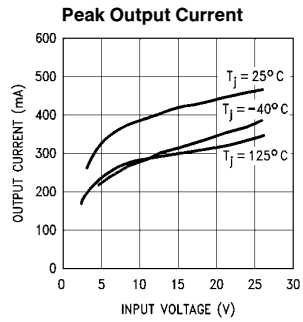
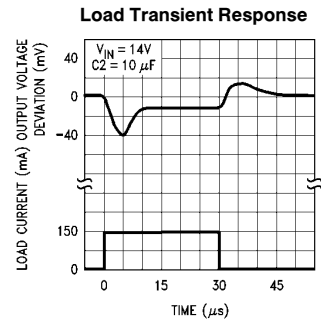
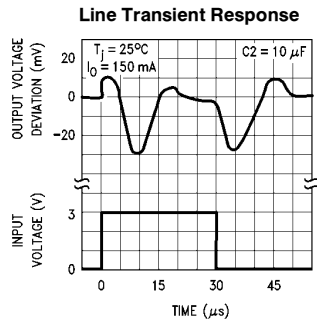
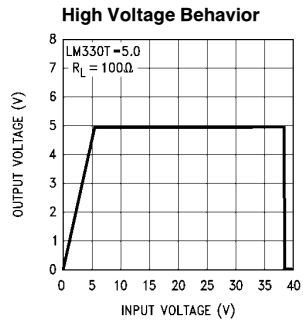
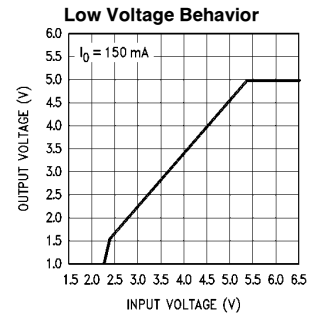
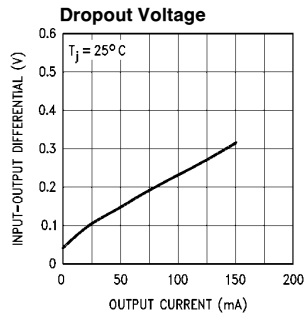
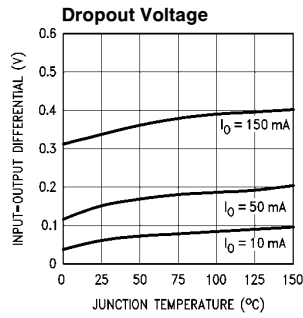
Internal Power Dissipation	Internally Limited
Operating Temperature Range	0°C to +70°C
Maximum Junction Temperature	+125°C
Storage Temperature Range	−65°C to +150°C
Lead Temperature (Soldering, 10 sec.)	+300°C

Electrical Characteristics (Note 1)

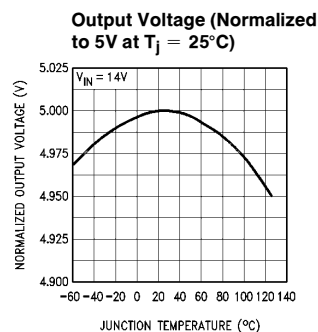
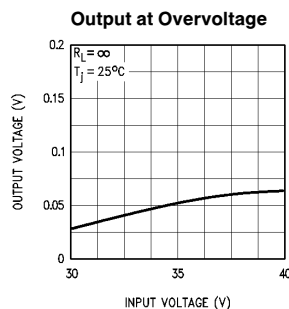
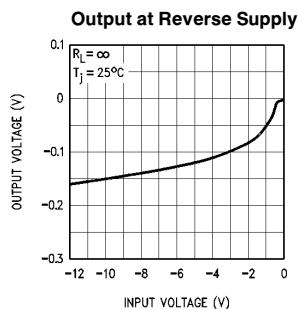
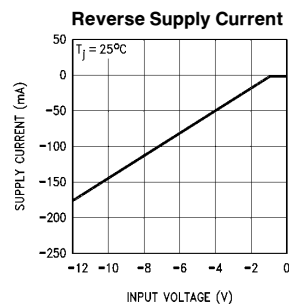
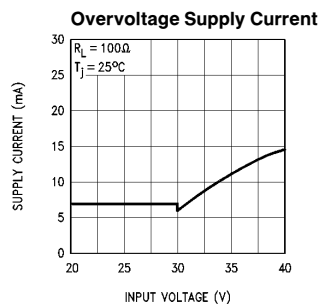
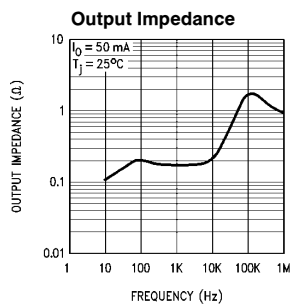
Symbol	Parameter	Conditions	Min	Typ	Max	Units
V_o	Output Voltage	$T_j = 25^\circ\text{C}$	4.8	5	5.2	V
	Output Voltage Over Temp	$5 < I_o < 150 \text{ mA}$ $6 < V_{IN} < 26\text{V}; 0^\circ\text{C} \leq T_j \leq 100^\circ\text{C}$	4.75		5.25	
ΔV_o	Line Regulation	$9 < V_{IN} < 16\text{V}, I_o = 5 \text{ mA}$ $6 < V_{IN} < 26\text{V}, I_o = 5 \text{ mA}$		7 30	25 60	mV
	Load Regulation	$5 < I_o < 150 \text{ mA}$		14	50	
	Long Term Stability			20		mV/1000 hrs
I_Q	Quiescent Current	$I_o = 10 \text{ mA}$ $I_o = 50 \text{ mA}$ $I_o = 150 \text{ mA}$		3.5 5 18	7 11 40	mA
	Line Transient Reverse Polarity	$V_{IN} = 40\text{V}, R_L = 100\Omega, 1\text{s}$ $V_{IN} = -6\text{V}, R_L = 100\Omega$		14 −80		
ΔI_Q	Quiescent Current Change	$6 < V_{IN} < 26\text{V}$		10		%
V_{IN}	Overvoltage Shutdown Voltage		26	38		V
	Max Line Transient			60		
		1s, $V_o \leq 5.5\text{V}$		50		
	Reverse Polarity Input Voltage			−30		
		DC $V_o > -0.3\text{V}, R_L = 100\Omega$		−12		
	Output Noise Voltage	10 Hz–100 kHz		50		μV
	Output Impedance	$I_o = 100 \text{ mADC} + 10 \text{ mArms}$		200		$\text{m}\Omega$
	Ripple Rejection			56		dB
	Current Limit		150	400	700	mA
	Dropout Voltage	$I_o = 150 \text{ mA}$		0.32	0.6	V
	Thermal Resistance	Junction to Case		4		$^\circ\text{C/W}$
		Junction to Ambient		50		

Note 1: Unless otherwise specified: $V_{IN} = 14\text{V}$, $I_o = 150 \text{ mA}$, $T_j = 25^\circ\text{C}$, $C1 = 0.1 \mu\text{F}$, $C2 = 10 \mu\text{F}$. All characteristics except noise voltage and ripple rejection are measured using pulse techniques ($t_W \leq 10 \text{ ms}$, duty cycle $\leq 5\%$). Output voltage changes due to changes in internal temperature must be taken into account separately.

Typical Performance Characteristics



Typical Performance Characteristics (Continued)

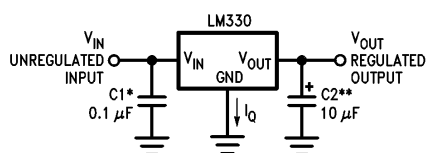


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Typical Applications

The LM330 is designed specifically to operate at lower input to output voltages. The device is designed utilizing a power lateral PNP transistor which reduces dropout voltage from 2.0V to 0.3V when compared to IC regulators using NPN pass transistors. Since the LM330 can operate at a much lower input voltage, the device power dissipation is reduced, heat sinking can be simpler and device reliability im-

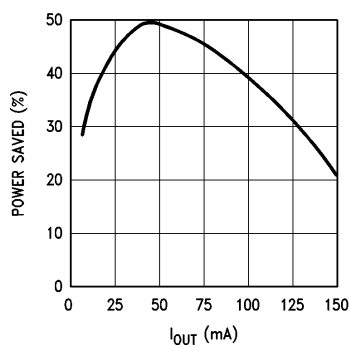
proved through lower chip operating temperature. Also, a cost savings can be utilized through use of lower power/voltage components. In applications utilizing battery power, the LM330 allows the battery voltage to drop to within 0.3V of output voltage prior to the voltage regulator dropping out of regulation.



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* Required if regulator is located far from power supply filter.

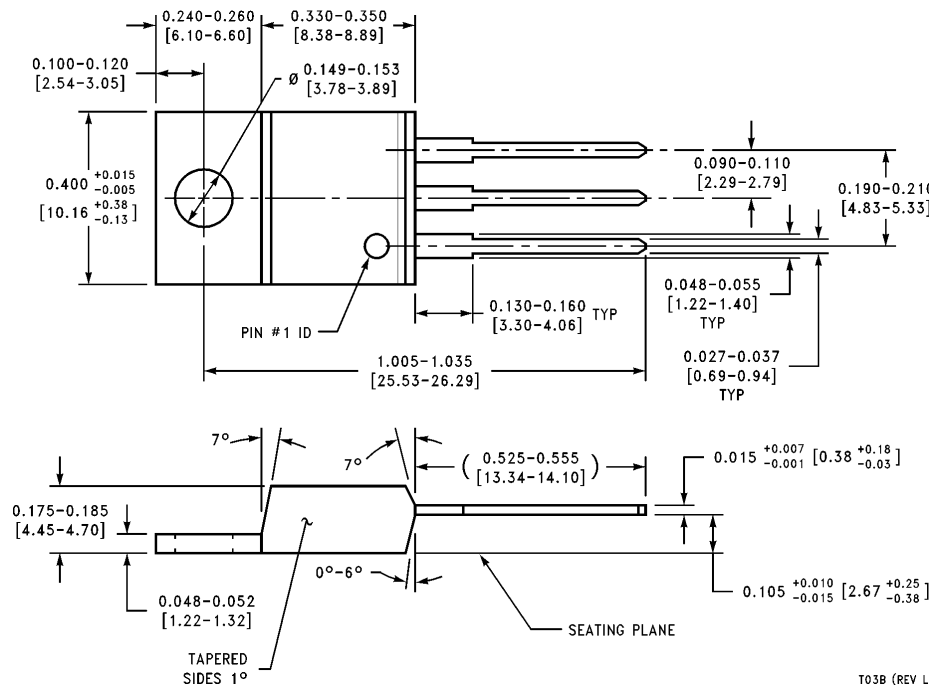
** C2 may be either an Aluminum or Tantalum type capacitor but must be rated to operate at -40°C to guarantee regulator stability to that temperature extreme. $10 \mu\text{F}$ is the minimum value required for stability and may be increased without bound. Locate as close as possible to the regulation.



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Note: Compared to IC regulator with 2.0V dropout voltage and $I_{Qmax} = 6.0 \text{ mA}$.



Physical Dimensions inches (millimeters)**LIFE SUPPORT POLICY**

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